Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 1-16.

17. (New) A method for producing a wafer comprising at least an ingot heat-treating step of subjecting a silicon single crystal in a state of an ingot to heat treatment, and a wafer processing step of processing the heat-treated ingot into wafers.

18. (New) The method for producing a wafer according to Claim 17, wherein in the ingot heat-treating step, bulk micro defects (BMDs) are formed in the silicon single crystal.

19. (New) The method for producing a wafer according to Claim 17, further comprising a wafer heat-treating step of subjecting the wafers to heat treatment after the wafer processing step.

20. (New) The method for producing a wafer according to Claim 18, further comprising a wafer heat-treating step of subjecting the wafers to heat treatment after the wafer processing step.

21. (New) The method for producing a wafer according to Claim 17, wherein in the wafer processing step, the heat-treated ingot is processed into mirror-like wafers.

22. (New) The method for producing a wafer according to Claim 21, further comprising an

epitaxial growth step of forming an epitaxial layer on the wafer after the processing into the mirror-like wafers.

23. (New) The method for producing a wafer according to Claim 17, wherein in the ingot heat-treating step, the silicon single crystal in a state of an ingot is subjected to heat treatment at 700 °C or more.

24. (New) The method for producing a wafer according to Claim 23, wherein in the ingot heat-treating step, the heat treatment is performed at a heat treatment temperature of 1100 °C or less for 30 minutes to 8 hours.

25. (New) The method for producing a wafer according to Claim 24, wherein in the ingot heat-treating step, the heat treatment is performed at a heat treatment temperature of 700 °C to 900 °C for 30 minutes to 8 hours.

26. (New) The method for producing a wafer according to Claim 17, wherein in the ingot heat-treating step, the heat treatment is performed at a temperature rising rate of 0.5 °C/min to 10 °C/min.

27. (New) The method for producing a wafer according to Claim 19, wherein in the wafer heat-treating step, a defect-free region (a DZ (denuded zone) layer) is formed in a surface of the wafer.

28. (New) The method for producing a wafer according to Claim 20, wherein in the wafer

heat-treating step, a defect-free region (a DZ (denuded zone) layer) is formed in a surface of the wafer.

29. (New) The method for producing a wafer according to Claim 19, wherein in the wafer heat-treating step, the heat treatment is performed at a heat treatment temperature of 900 °C to 1300 °C for 5 minutes to 16 hours.

30. (New) The method for producing a wafer according to Claim 20, wherein in the wafer heat-treating step, the heat treatment is performed at a heat treatment temperature of 900 °C to 1300 °C for 5 minutes to 16 hours.

31. (New) The method for producing a wafer according to Claim 19, wherein in the wafer heat-treating step, the temperature is raised at a temperature rising rate of 5 °C/min or more.

32. (New) The method for producing a wafer according to Claim 20, wherein in the wafer heat-treating step, the temperature is raised at a temperature rising rate of 5 °C/min or more.

33. (New) The method for producing a wafer according to Claim 22, wherein the epitaxial growth step is that after a pretreatment is performed at a temperature of 1000 °C or more, the epitaxial growth is performed at a temperature of 1000 °C or more.

34. (New) The method for producing a wafer according to Claim 17, wherein the silicon single crystal is a crystal doped with nitrogen.

35. (New) The method for producing a wafer according to Claim 17, wherein the silicon single crystal is a crystal in a nearly perfect crystal (NPC) region produced by Czochralski method.

36. (New) The method for producing a wafer according to Claim 17, wherein the silicon single crystal in a state of an ingot is an ingot pulled by a single crystal-pulling apparatus according to Czochralski method as it is or an ingot in a state that the pulled ingot is cylindrically ground and cut in a shape of a block.